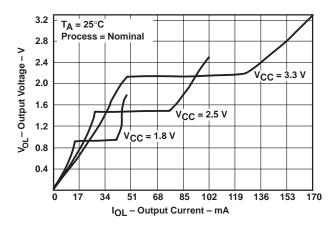
- EPIC<sup>™</sup> (Enhanced-Performance Implanted CMOS) Submicron Process
- DOC<sup>™</sup> (Dynamic Output Control) Circuit Dynamically Changes Output Impedance, Resulting in Noise Reduction Without Speed Degradation
- Dynamic Drive Capability Is Equivalent to Standard Outputs With I<sub>OH</sub> and I<sub>OL</sub> of ±24 mA at 2.5-V V<sub>CC</sub>
- Overvoltage-Tolerant Inputs/Outputs Allow Mixed-Voltage-Mode Data Communications
- I<sub>off</sub> Supports Partial-Power-Down Mode Operation
- Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages

## description

A Dynamic Output Control (DOC) circuit is implemented, which, during the transition, initially lowers the output impedance to effectively drive the load and, subsequently, raises the impedance to reduce noise. Figure 1 shows typical V<sub>OL</sub> vs I<sub>OL</sub> and V<sub>OH</sub> vs I<sub>OH</sub> curves to illustrate the output impedance and drive capability of the circuit. At the beginning of the signal transition, the DOC circuit provides a maximum dynamic drive that is equivalent to a high-drive standard-output device. For more information, refer to the TI application reports, *AVC Logic Family Technology and Applications*, literature number SCEA006, and *Dynamic Output Control (DOC*<sup>TM</sup>) *Circuitry Technology and Applications*, literature number SCEA009.



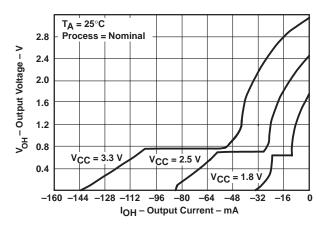


Figure 1. Output Voltage vs Output Current

This quadruple 2-input positive-OR gate is operational at 1.2-V to 3.6-V  $V_{CC}$ , but is designed specifically for 1.65-V to 3.6-V  $V_{CC}$  operation.

The SN74AVC32 performs the Boolean function  $Y = \overline{\overline{A} \bullet \overline{B}}$  or Y = A + B in positive logic.

This device is fully specified for partial-power-down applications using I<sub>off</sub>. The I<sub>off</sub> circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74AVC32 is characterized for operation from -40°C to 85°C.



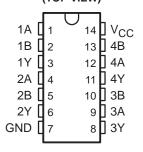
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## terminal assignments

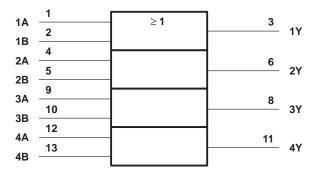
# D, DGV, OR PW PACKAGE (TOP VIEW)



# FUNCTION TABLE (each gate)

INP	UTS	OUTPUT			
Α	В	Y			
Н	Χ	Н			
Х	Н	Н			
L	L	L			

# logic symbol†



<sup>&</sup>lt;sup>†</sup>This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

## logic diagram, each gate (positive logic)



# absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub>	0.5 V to 4.6 V
Input voltage range, V <sub>I</sub> (see Note 1)	
Output voltage range, VO (see Notes 1 and 2)	$\dots$ -0.5 V to V <sub>CC</sub> + 0.5 V
Input clamp current, $I_{ K }(V_{ } < 0)$	
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through each V <sub>CC</sub> or GND	±100 mA
Package thermal impedance, θ <sub>JA</sub> (see Note 3): D package	86°C/W
DGV package	127°C/W
PW package	113°C/W
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. The output positive-voltage rating may be exceeded up to 4.6 V maximum if the output current rating is observed.
- 3. The package thermal impedance is calculated in accordance with JESD 51.

# **QUADRUPLE 2-INPUT POSITIVE-OR GATE**

SCES149E - DECEMBER 1998 - REVISED FEBRUARY 2000

## recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
V	Cumply voltage	Operating	1.4	3.6	V	
Vcc	Supply voltage	Data retention only	1.2		V	
		V <sub>CC</sub> = 1.2 V	VCC			
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	0.65 × V <sub>CC</sub>			
$\vee_{IH}$	High-level input voltage	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V <sub>CC</sub>		V	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7			
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2			
		V <sub>CC</sub> = 1.2 V		GND		
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		0.35 × V <sub>CC</sub>		
VIL	Low-level input voltage	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	V	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7		
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		0.8		
VI	Input voltage		0	3.6	V	
V <sub>O</sub> O	Output voltage	Active state	0	VCC	V	
	Output voltage	3-state	0	3.6	ı v	
		V <sub>CC</sub> = 1.4 V to 1.6 V		-2		
laura	Static high-level output current <sup>†</sup>	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-4	mA	
IOHS	Static riigh-level output current	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-8		
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		-12		
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2		
lava	Static low-level output current <sup>†</sup>	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		4	mA	
IOLS	Static low-level output current	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		8		
		V <sub>CC</sub> = 3 V to 3.6 V		12		
Δt/Δν	Input transition rise or fall rate	V <sub>CC</sub> = 1.4 V to 3.6 V		5	ns/V	
TA	Operating free-air temperature		-40	85	°C	

<sup>†</sup> Dynamic drive capability is equivalent to standard outputs with IOH and IOL of ±24 mA at 2.5-V VCC. See Figure 1 for VOL vs IOL and VOH vs IOH characteristics. Refer to the TI application reports, AVC Logic Family Technology and Applications, literature number SCEA006, and Dynamic Output Control (DOC™) Circuitry Technology and Applications, literature number SCEA009.

NOTE 4: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



# PRODUCT PREVIEW

# electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST	CONDITIONS	Vcc	MIN	TYP†	MAX	UNIT
	I <sub>OHS</sub> = -100 μA		1.4 V to 3.6 V	V <sub>CC</sub> -0.	.2		
	$I_{OHS} = -2 \text{ mA},$	V <sub>IH</sub> = 0.91 V	1.4 V	1.05			
Voн	$I_{OHS} = -4 \text{ mA},$	V <sub>IH</sub> = 1.07 V	1.65 V	1.2			V
	$I_{OHS} = -8 \text{ mA},$	V <sub>IH</sub> = 1.7 V	2.3 V	1.75			
	I <sub>OHS</sub> = -12 mA,	V <sub>IH</sub> = 2 V	3 V	2.3			
	I <sub>OLS</sub> = 100 μA		1.4 V to 3.6 V			0.2	
	IOLS = 2 mA,	V <sub>IL</sub> = 0.49 V	1.4 V			0.4	V
V <sub>OL</sub>	I <sub>OLS</sub> = 4 mA,	V <sub>IL</sub> = 0.57 V	1.65 V			0.45	
	I <sub>OLS</sub> = 8 mA,	V <sub>IL</sub> = 0.7 V	2.3 V			0.55	
	I <sub>OLS</sub> = 12 mA,	V <sub>IL</sub> = 0.8 V	3 V			0.7	
I <sub>I</sub>	$V_I = V_{CC}$ or GND		3.6 V			±2.5	μΑ
l <sub>off</sub>	$V_I$ or $V_O = 3.6 V$		0			±10	μΑ
Icc	$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			40	μΑ
C.	V- V or CND		2.5 V				~F
C <sub>i</sub>	$V_I = V_{CC}$ or GND	3.3 V				pF	

<sup>†</sup> Typical values are measured at  $T_A = 25$ °C.

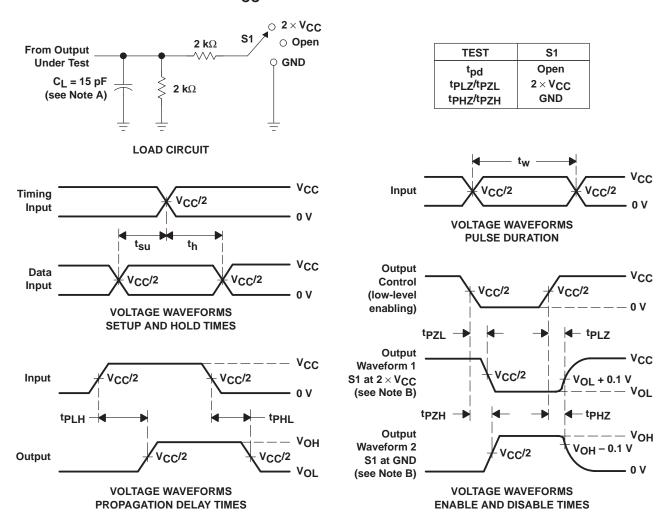
# switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 1.2 \text{ V}$ $V_{CC} = 1.5 \text{ V}$ $\pm 0.1 \text{ V}$		V <sub>CC</sub> = 1.8 V ± 0.15 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		UNIT	
			TYP	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A or B	Υ										ns

# operating characteristics, T<sub>A</sub> = 25°C

PARAMETER		TEST CONDITIONS	V <sub>CC</sub> = 1.8 V	$V_{CC} = 2.5 V$	V <sub>CC</sub> = 3.3 V	UNIT
	FARAIMETER			TYP	UNIT	
C <sub>pd</sub>	Power dissipation capacitance per gate	$C_L = 0$ , $f = 10 \text{ MHz}$				pF

# PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.2 \text{ V}$ AND 1.5 V $\pm$ 0.1 V



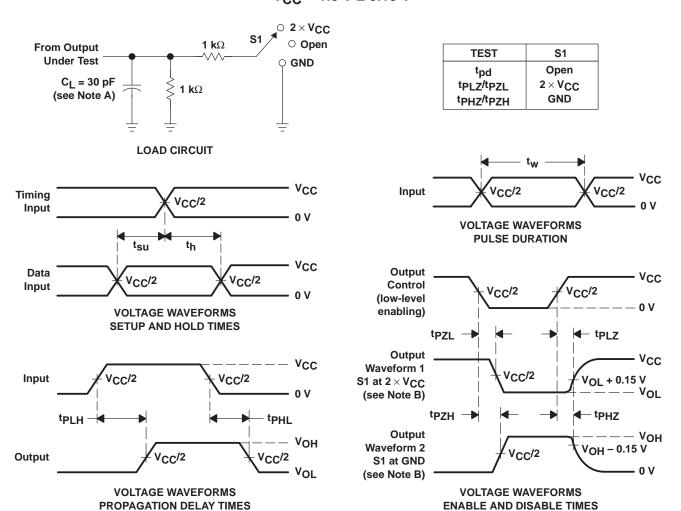
NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50~\Omega$ ,  $t_f \leq$  2 ns,  $t_f \leq$  2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms



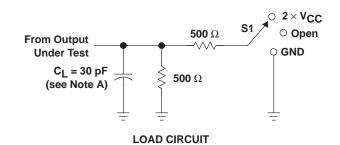
# PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$

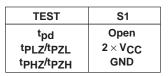


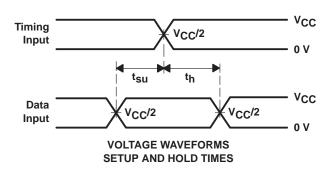
- NOTES: A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f \leq 2$  ns,  $t_f \leq 2$  ns.
  - D. The outputs are measured one at a time with one transition per measurement.
  - E. tpLZ and tpHZ are the same as tdis.
  - F. tpzL and tpzH are the same as ten.
  - G. tpLH and tpHL are the same as tpd.

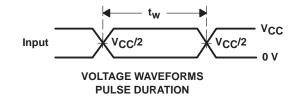
Figure 3. Load Circuit and Voltage Waveforms

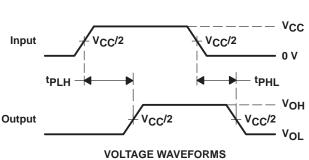
## PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 V \pm 0.2 V$



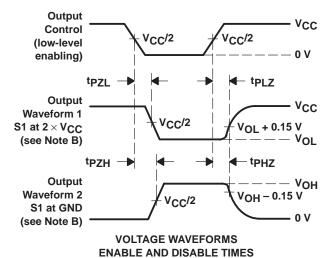








**PROPAGATION DELAY TIMES** 



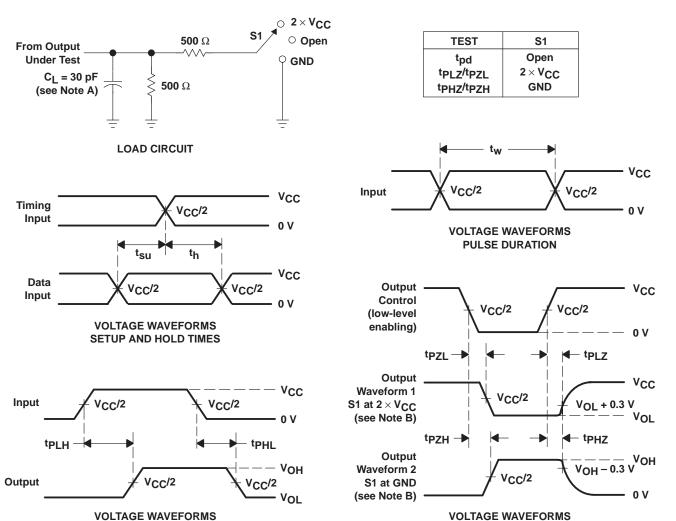
NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_Q = 50 \Omega$ ,  $t_f \leq$  2 ns,  $t_f \leq$  2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.

Figure 4. Load Circuit and Voltage Waveforms

**ENABLE AND DISABLE TIMES** 

# PARAMETER MEASUREMENT INFORMATION $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$



- NOTES: A. C<sub>I</sub> includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f \leq 2$  ns.
  - D. The outputs are measured one at a time with one transition per measurement.
  - E. tpl 7 and tpH7 are the same as tdis.

PROPAGATION DELAY TIMES

- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G. tpLH and tpHL are the same as tpd.

Figure 5. Load Circuit and Voltage Waveforms

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